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REVISION HISTORY

6/10—Revision 0: Initial Version

The AD822-EP drives up to 350 pF of direct capacitive load as a follower and provides a minimum output current of 15 mA. This allows the amplifier to handle a wide range of load conditions. Its combination of ac and dc performance, plus the outstanding load drive capability, results in an exceptionally versatile amplifier for the single-supply user.

The AD822-EP operates over the military temperature range of -55° C to $+125^{\circ}$ C.

The AD822-EP is offered in an 8-lead SOIC_N package.

Full details about this enhanced product are available in the AD822 data sheet, which should be consulted in conjunction with this data sheet.

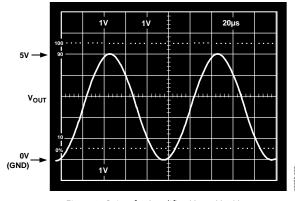


Figure 3. Gain-of-2 Amplifier; $V_s = 5 V$, 0 V, $V_{IN} = 2.5 V$ Sine Centered at 1.25 V, $R_L = 100 \Omega$

SPECIFICATIONS

 V_{S} = 0 V, 5 V @ T_{A} = 25°C, V_{CM} = 0 V, V_{OUT} = 0.2 V, unless otherwise noted.

Table 1.

			T Grade	9	
Parameter	Test Conditions/Comments	Min	Тур	Мах	Unit
DC PERFORMANCE					
Initial Offset			0.1	0.8	mV
Maximum Offset Over Temperature			0.5	1.2	mV
Offset Drift			2		μV/°C
Input Bias Current	$V_{CM} = 0 V to 4 V$		2	25	pА
At T _{MAX}			0.5	6	nA
Input Offset Current			2	20	pА
At T _{MAX}			0.5		nA
Open-Loop Gain	$V_{OUT} = 0.2 V \text{ to } 4 V$				
	$R_L = 100 \ k\Omega$	500	1000		V/mV
T _{MIN} to T _{MAX}		400			V/mV
	$R_L = 10 \ k\Omega$	80	150		V/mV
T _{MIN} to T _{MAX}		80			V/mV
	$R_L = 1 \ k\Omega$	15	30		V/mV
T _{MIN} to T _{MAX}		10			V/mV
NOISE/HARMONIC PERFORMANCE					
Input Voltage Noise					
f = 0.1 Hz to 10 Hz			2		μV p-p
f = 10 Hz			25		nV/√Hz
f = 100 Hz			21		nV/√Hz
f = 1 kHz			16		nV/√Hz
f = 10 kHz			13		nV/√Hz
Input Current Noise					
f = 0.1 Hz to 10 Hz			18		fA p-p
f = 1 kHz			0.8		fA/√Hz
Harmonic Distortion	$R_L = 10 \text{ k}\Omega \text{ to } 2.5 \text{ V}$				
f = 10 kHz	$V_{OUT} = 0.25 V \text{ to } 4.75 V$		-93		dB
DYNAMIC PERFORMANCE					
Unity-Gain Frequency			1.8		MHz
Full Power Response	$V_{OUT} p - p = 4.5 V$		210		kHz
Slew Rate			3		V/µs
Settling Time					
То 0.1%	$V_{OUT} = 0.2 V \text{ to } 4.5 V$		1.4		μs
To 0.01%	$V_{OUT} = 0.2 V \text{ to } 4.5 V$		1.8		μs
MATCHING CHARACTERISTICS					
Initial Offset				1.0	mV
Maximum Offset Over Temperature				1.6	mV
Offset Drift			3		µV/°C
Input Bias Current				20	pA
Crosstalk @ f = 1 kHz	$R_L = 5 k\Omega$		-130		dB
Crosstalk @ f = 100 kHz	$R_L = 5 k\Omega$		-93		dB

			T Grade		
Parameter	Test Conditions/Comments	Min	Тур	Мах	Unit
INPUT CHARACTERISTICS					
Input Voltage Range ¹ , T _{MIN} to T _{MAX}		-0.2		+4	V
Common-Mode Rejection Ratio (CMRR)	$V_{CM} = 0 V \text{ to } 2 V$	66	80		dB
T _{MIN} to T _{MAX}	$V_{CM} = 0 V \text{ to } 2 V$	66			dB
Input Impedance					
Differential			10 ¹³ 0.5		Ω∥pF
Common Mode			10 ¹³ 2.8		Ω pF
OUTPUT CHARACTERISTICS					
Output Saturation Voltage ²					
Vol – Vee	$I_{SINK} = 20 \ \mu A$		5	7	mV
T _{MIN} to T _{MAX}				10	mV
V _{CC} – V _{OH}	$I_{SOURCE} = 20 \ \mu A$		10	14	mV
T _{MIN} to T _{MAX}				20	mV
$V_{OL} - V_{EE}$	$I_{SINK} = 2 \text{ mA}$		40	55	mV
T _{MIN} to T _{MAX}				80	mV
V _{CC} – V _{OH}	$I_{SOURCE} = 2 \text{ mA}$		80	110	mV
T _{MIN} to T _{MAX}				160	mV
$V_{OL} - V_{EE}$	$I_{SINK} = 15 \text{ mA}$		300	500	mV
T _{MIN} to T _{MAX}				1000	mV
V _{CC} – V _{OH}	I _{SOURCE} = 15 mA		800	1500	mV
T _{MIN} to T _{MAX}				1900	mV
Operating Output Current		15			mA
T _{MIN} to T _{MAX}		12			mA
Capacitive Load Drive			350		pF
POWER SUPPLY					
Quiescent Current, T _{MIN} to T _{MAX}			1.24	1.6	mA
Power Supply Rejection	V+ = 5 V to 15 V	66	80		dB
T _{MIN} to T _{MAX}		66			dB

¹ This is a functional specification. Amplifier bandwidth decreases when the input common-mode voltage is driven in the range (V+ – 1 V) to V+. Common-mode error voltage is typically less than 5 mV with the common-mode voltage set at 1 V below the positive supply. ² V_{OL} – V_{EE} is defined as the difference between the lowest possible output voltage (V_{OL}) and the negative voltage supply rail (V_{EE}). V_{CC} – V_{OH} is defined as the difference between the lowest possible output voltage (V_{OL}) and the negative voltage supply rail (V_{EE}). V_{CC} – V_{OH} is defined as the difference between the lowest possible output voltage (V_{OL}) and the negative voltage supply rail (V_{EE}). V_{CC} – V_{OH} is defined as the difference between the lowest possible output voltage (V_{OL}) and the negative voltage supply rail (V_{EE}). V_{CC} – V_{OH} is defined as the difference between the lowest possible output voltage (V_{OL}) and the negative voltage supply rail (V_{EE}). V_{CC} – V_{OH} is defined as the difference between the lowest possible output voltage (V_{OL}) and the negative voltage supply rail (V_{EE}). V_{CC} – V_{OH} is defined as the difference between the lowest possible output voltage (V_{OL}) and the negative voltage supply rail (V_{EE}).

between the highest possible output voltage (V_{OH}) and the positive supply voltage (V_{CC}).

 $V_{\text{S}}=\pm5$ V @ $T_{\text{A}}=25^{\circ}\text{C},$ V_{CM} = 0 V, V_{OUT} = 0 V, unless otherwise noted.

Table 2.

				T Grade		
Parameter	Test Conditions/Comments	Min	Тур	Мах	Unit	
DC PERFORMANCE						
Initial Offset			0.1	0.8	mV	
Maximum Offset Over Temperature			0.5	1.5	mV	
Offset Drift			2		μV/°C	
Input Bias Current	$V_{CM} = -5 V \text{ to } +4 V$		2	25	pА	
At T _{MAX}			0.5	6	nA	
Input Offset Current			2	20	pА	
At T _{MAX}			0.5		nA	
Open-Loop Gain	$V_{OUT} = -4 V \text{ to } +4 V$					
	$R_L = 100 \text{ k}\Omega$	400	1000		V/mV	
T _{MIN} to T _{MAX}		400			V/mV	
	$R_L = 10 \ k\Omega$	80	150		V/mV	
T _{MIN} to T _{MAX}		80			V/mV	
	$R_L = 1 k\Omega$	20	30		V/mV	
T _{MIN} to T _{MAX}		10			V/mV	
NOISE/HARMONIC PERFORMANCE						
Input Voltage Noise						
f = 0.1 Hz to 10 Hz			2		μV p-p	
f = 10 Hz			25		nV/√Hz	
f = 100 Hz			21		nV/√Hz	
f = 1 kHz			16		nV/√Hz	
f = 10 kHz			13		nV/√Hz	
Input Current Noise						
f = 0.1 Hz to 10 Hz			18		fA p-p	
f = 1 kHz			0.8		fA/√Hz	
Harmonic Distortion	$R_L = 10 \ k\Omega$					
f = 10 kHz	$V_{OUT} = \pm 4.5 V$		-93		dB	
DYNAMIC PERFORMANCE						
Unity-Gain Frequency			1.9		MHz	
Full Power Response	V _{оит} р-р = 9 V		105		kHz	
Slew Rate			3		V/µs	
Settling Time			J		1, p.5	
to 0.1%	$V_{OUT} = 0 V \text{ to } \pm 4.5 V$		1.4		μs	
to 0.01%	$V_{OUT} = 0 V \text{ to } \pm 4.5 V$		1.8		μs	
MATCHING CHARACTERISTICS			110		~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~	
Initial Offset				1.0	mV	
Maximum Offset Over Temperature				3	mV	
Offset Drift			3	5	μV/°C	
Input Bias Current			2	25	pA	
Crosstalk @ $f = 1 \text{ kHz}$	$R_L = 5 k\Omega$		-130	23	dB	
Crosstalk @ $f = 100 \text{ kHz}$	$R_L = 5 k\Omega$		-93		dB	
INPUT CHARACTERISTICS						
Input Voltage Range ¹ , T_{MIN} to T_{MAX}		-5.2		+4	v	
Common-Mode Rejection Ratio (CMRR)	$V_{CM} = -5 V \text{ to } +2 V$	-5.2 66	80	+4	v dB	
	$V_{CM} = -5 V \text{ to } +2 V$ $V_{CM} = -5 V \text{ to } +2 V$	66	00		dB	
Input Impedance	$v_{CM} = -3 v (0 + 2 v)$	00			UB	
Differential			1013110 E			
			10 ¹³ 0.5		Ω pF	
Common Mode			1013 2.8		Ω∥pF	

			T Grad	e	
Parameter	Test Conditions/Comments	Min	Тур	Мах	Unit
OUTPUT CHARACTERISTICS					
Output Saturation Voltage ²					
$V_{OL} - V_{EE}$	$I_{SINK} = 20 \ \mu A$		5	7	mV
T _{MIN} to T _{MAX}				10	mV
$V_{CC} - V_{OH}$	$I_{SOURCE} = 20 \ \mu A$		10	14	mV
T _{MIN} to T _{MAX}				20	mV
$V_{OL} - V_{EE}$	$I_{SINK} = 2 \text{ mA}$		40	55	mV
T _{MIN} to T _{MAX}				80	mV
$V_{CC} - V_{OH}$	$I_{SOURCE} = 2 \text{ mA}$		80	110	mV
T _{MIN} to T _{MAX}				160	mV
$V_{OL} - V_{EE}$	I _{SINK} = 15 mA		300	500	mV
T _{MIN} to T _{MAX}				1000	mV
V _{CC} – V _{OH}	Isource = 15 mA		800	1500	mV
T _{MIN} to T _{MAX}				1900	mV
Operating Output Current		15			mA
T _{MIN} to T _{MAX}		12			mA
Capacitive Load Drive			350		pF
POWER SUPPLY					
Quiescent Current, T _{MIN} to T _{MAX}			1.3	1.6	mA
Power Supply Rejection	$V_{SY} = \pm 5 V \text{ to } \pm 15 V$	66	80		dB
T _{MIN} to T _{MAX}		66			dB

¹ This is a functional specification. Amplifier bandwidth decreases when the input common-mode voltage is driven in the range (V+ -1 V) to V+. Common-mode error voltage is typically less than 5 mV with the common-mode voltage set at 1 V below the positive supply. ² V_{OL} - V_{EE} is defined as the difference between the lowest possible output voltage (V_{OL}) and the negative voltage supply rail (V_{EE}). V_{CC} - V_{OH} is defined as the difference between the highest possible output voltage (V_{OH}) and the positive supply voltage (V_{CC}).

 $V_{\text{S}}=\pm 15$ V @ $T_{\text{A}}=25^{\circ}\text{C},$ $V_{\text{CM}}=0$ V, $V_{\text{OUT}}=0$ V, unless otherwise noted.

Table 3.

			T Grade		
Parameter	Test Conditions/Comments	Min	Тур	Мах	Unit
DC PERFORMANCE					
Initial Offset			0.4	2	mV
Maximum Offset Over Temperature			0.5	3	mV
Offset Drift			2		μV/°C
Input Bias Current	$V_{CM} = 0 V$		2	25	pА
	$V_{CM} = -10 V$		40		pА
At T _{MAX}	$V_{CM} = 0 V$		0.5	6	nA
Input Offset Current			2	20	pА
At T _{MAX}			0.5		nA
Open-Loop Gain	$V_{OUT} = -10 V to + 10 V$				
	$R_L = 100 \ k\Omega$	500	2000		V/mV
T _{MIN} to T _{MAX}		500			V/mV
	$R_L = 10 \ k\Omega$	100	500		V/mV
T _{MIN} to T _{MAX}		100			V/mV
	$R_L = 1 k\Omega$	30	45		V/mV
Tmin to Tmax		20			V/mV
VOISE/HARMONIC PERFORMANCE					1
Input Voltage Noise					
f = 0.1 Hz to 10 Hz			2		μV р-р
f = 10 Hz			25		nV/√Hz
f = 100 Hz			21		nV/√Hz
f = 1 kHz			16		nV/√Hz
f = 10 kHz			13		nV/√Hz
Input Current Noise			15		,
f = 0.1 Hz to 10 Hz			18		fA p-p
f = 1 kHz			0.8		fA/√Hz
Harmonic Distortion	$R_L = 10 \text{ k}\Omega$		0.0		17 0 1112
f = 10 kHz	$V_{OUT} = \pm 10 \text{ V}$		-85		dB
DYNAMIC PERFORMANCE	V001-±10V		05		ab
Unity-Gain Frequency			1.9		MHz
Full Power Response	V _{оит} р-р = 20 V		1.9 45		kHz
Slew Rate	vour p-p – 20 v		45 3		κπz V/μs
Settling Time			2		v/µs
to 0.1%	$V_{OUT} = 0 V \text{ to } \pm 10 V$		4.1		
to 0.01%	$V_{OUT} = 0 V to \pm 10 V$ $V_{OUT} = 0 V to \pm 10 V$		4.1 4.5		μs
			4.J		μs
				2	
Initial Offset				3	mV
Maximum Offset Over Temperature			2	4	mV
Offset Drift			3	25	μV/°C
Input Bias Current			120	25	pA
Crosstalk @ $f = 1 \text{ kHz}$	$R_L = 5 k\Omega$		-130		dB
Crosstalk @ f = 100 kHz	$R_L = 5 k\Omega$		-93		dB
NPUT CHARACTERISTICS					
Input Voltage Range ¹ , T _{MIN} to T _{MAX}		-15.2		+14	V
Common-Mode Rejection Ratio (CMRR)	$V_{CM} = -15 V \text{ to } +12 V$	70	80		dB
T _{MIN} to T _{MAX}	$V_{CM} = -15 V \text{ to } +12 V$	70			dB
Input Impedance					
Differential			10 ¹³ 0.5		Ω∥pF
Common Mode			10 ¹³ 2.8		Ω∥pF

			T Grade		
Parameter	Test Conditions/Comments	Min	Тур	Max	Unit
OUTPUT CHARACTERISTICS					
Output Saturation Voltage ²					
$V_{OL} - V_{EE}$	I _{SINK} = 20 μA		5	7	mV
T _{MIN} to T _{MAX}				10	mV
$V_{CC} - V_{OH}$	$I_{SOURCE} = 20 \ \mu A$		10	14	mV
T _{MIN} to T _{MAX}				20	mV
$V_{OL} - V_{EE}$	$I_{SINK} = 2 \text{ mA}$		40	55	mV
T _{MIN} to T _{MAX}				80	mV
$V_{CC} - V_{OH}$	$I_{SOURCE} = 2 \text{ mA}$		80	110	mV
T _{MIN} to T _{MAX}				160	mV
$V_{OL} - V_{EE}$	I _{SINK} = 15 mA		300	500	mV
T _{MIN} to T _{MAX}				1000	mV
V _{CC} – V _{OH}	Isource = 15 mA		800	1500	mV
T _{MIN} to T _{MAX}				1900	mV
Operating Output Current		20			mA
T _{MIN} to T _{MAX}		15			mA
Capacitive Load Drive			350		pF
POWER SUPPLY					
Quiescent Current, T _{MIN} to T _{MAX}			1.4	1.8	mA
Power Supply Rejection	$V_{SY} = \pm 5 V \text{ to } \pm 15 V$	70	80		dB
T _{MIN} to T _{MAX}		70			dB

¹ This is a functional specification. Amplifier bandwidth decreases when the input common-mode voltage is driven in the range (V+ -1 V) to V+. Common-mode error voltage is typically less than 5 mV with the common-mode voltage set at 1 V below the positive supply. ² V_{OL} - V_{EE} is defined as the difference between the lowest possible output voltage (V_{OL}) and the negative voltage supply rail (V_{EE}). V_{CC} - V_{OH} is defined as the difference between the highest possible output voltage (V_{OH}) and the positive supply voltage (V_{CC}).

ABSOLUTE MAXIMUM RATINGS

Table 4.

Parameter	Rating
Supply Voltage	±18 V
Internal Power Dissipation	
8-Lead SOIC_N (R)	Observe Maximum Junction Temperature
Input Voltage	((V+) + 0.2 V) to ((V–) – 20 V)
Output Short-Circuit Duration	Indefinite
Differential Input Voltage	±30 V
Storage Temperature Range (R)	–65°C to +150°C
Operating Temperature Range	–55°C to +125°C
Maximum Junction Temperature	150°C
Lead Temperature (Soldering, 60 sec)	260°C

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

THERMAL RESISTANCE

 θ_{JA} is specified for the worst-case conditions, that is, a device soldered in a circuit board for surface-mount packages.

Table 5. Thermal Resistance

Package Type	θ _{JA}	οıc	Unit
8-lead SOIC_N (R)	160	43	°C/W

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

TYPICAL PERFORMANCE CHARACTERISTICS

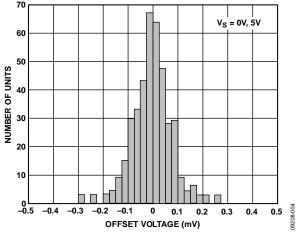


Figure 4. Typical Distribution of Offset Voltage (390 Units)

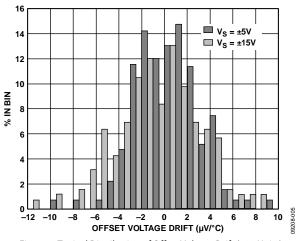


Figure 5. Typical Distribution of Offset Voltage Drift (100 Units)

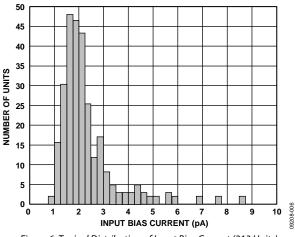


Figure 6. Typical Distribution of Input Bias Current (213 Units)

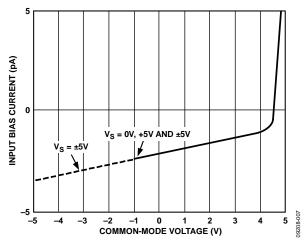


Figure 7. Input Bias Current vs. Common-Mode Voltage; V_s = 5 V, 0 V, and $V_s = \pm 5 V$

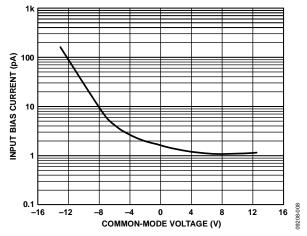


Figure 8. Input Bias Current vs. Common-Mode Voltage; $V_S = \pm 15 V$

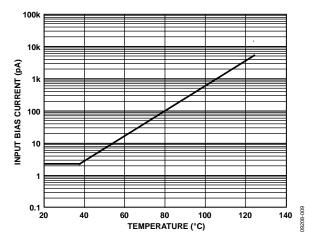


Figure 9. Input Bias Current vs. Temperature; $V_S = 5 V$, $V_{CM} = 0 V$

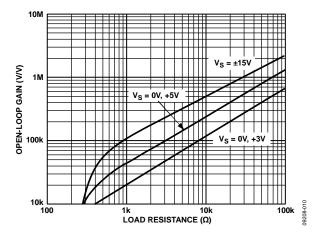


Figure 10. Open-Loop Gain vs. Load Resistance

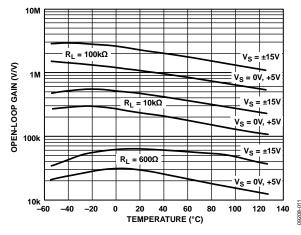


Figure 11. Open-Loop Gain vs. Temperature

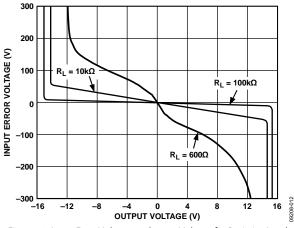


Figure 12. Input Error Voltage vs. Output Voltage for Resistive Loads

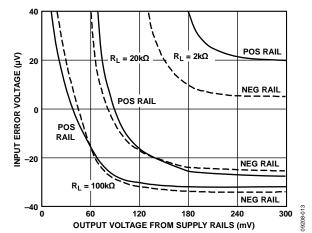
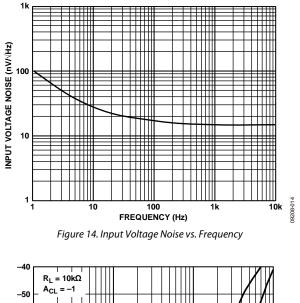


Figure 13. Input Error Voltage with Output Voltage Within 300 mV of Either Supply Rail for Various Resistive Loads; $V_S = \pm 5 V$



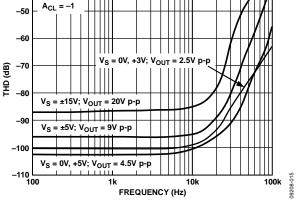


Figure 15. Total Harmonic Distortion (THD) vs. Frequency

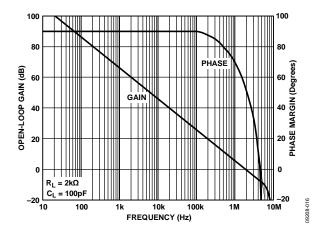
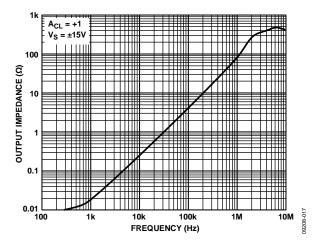
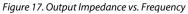


Figure 16. Open-Loop Gain and Phase Margin vs. Frequency





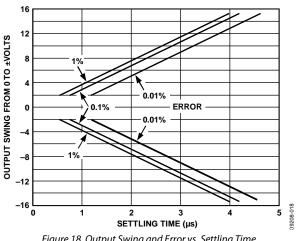
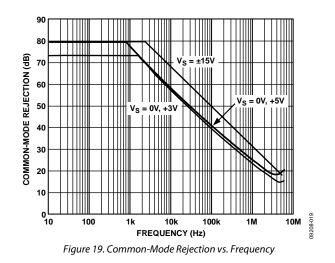


Figure 18. Output Swing and Error vs. Settling Time



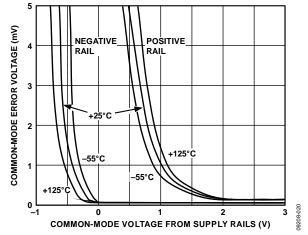


Figure 20. Absolute Common-Mode Error vs. Common-Mode Voltage from Supply Rails (Vs - VCM)

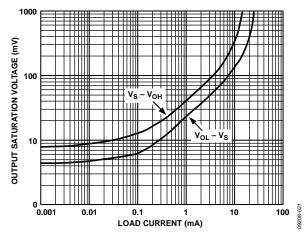
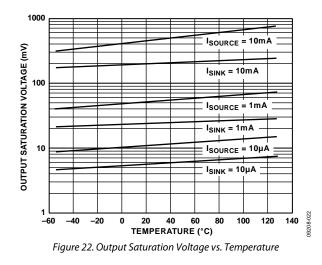
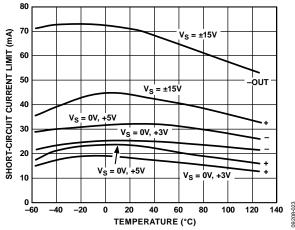


Figure 21. Output Saturation Voltage vs. Load Current







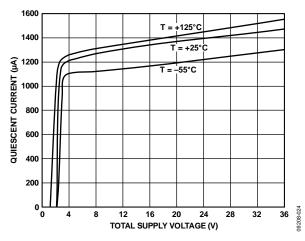
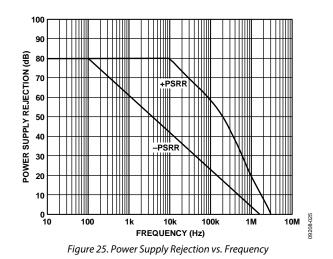
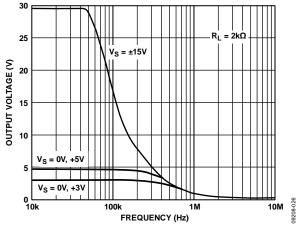
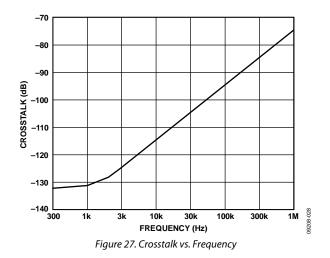


Figure 24. Quiescent Current vs. Supply Voltage vs. Temperature









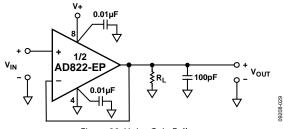


Figure 28. Unity-Gain Follower

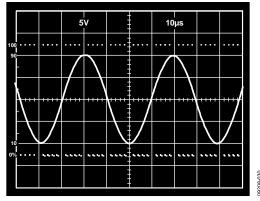
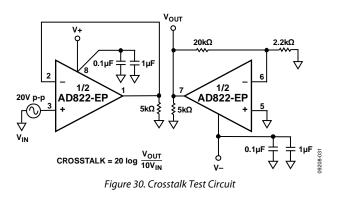


Figure 29. 20 V p-p, 25 kHz Sine Wave Input; Unity-Gain Follower; V_s = ± 15 V, $R_L = 600 \Omega$



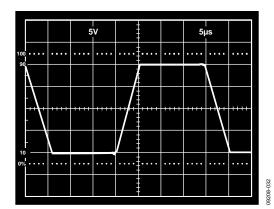


Figure 31. Large Signal Response Unity-Gain Follower; $V_S = \pm 15 V$, $R_L = 10 k\Omega$

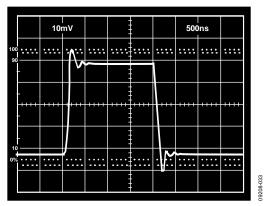


Figure 32. Small Signal Response Unity-Gain Follower; $V_S = \pm 15 V$, $R_L = 10 k\Omega$

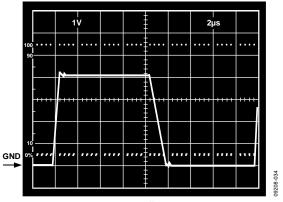


Figure 33. V_s = 5 V, 0 V; Unity-Gain Follower Response to 0 V to 4 V Step

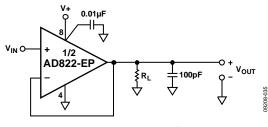
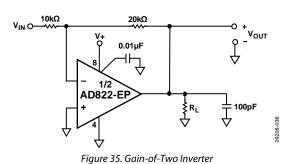


Figure 34. Unity-Gain Follower



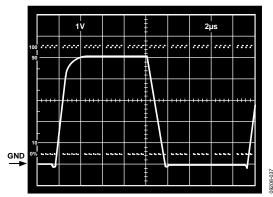


Figure 36. $V_5 = 5 V$, 0 V; Unity-Gain Follower Response to 0 V to 5 V Step

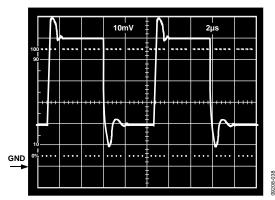


Figure 37. $V_S = 5 V$, 0 V; Unity-Gain Follower Response to 40 mV Step, Centered 40 mV above Ground, $R_L = 10 k\Omega$

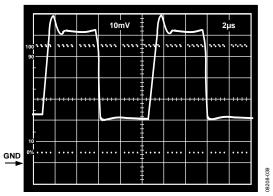


Figure 38. $V_S = 5 V$, 0 V; Gain-of-2 Inverter Response to 20 mV Step, Centered 20 mV Below Ground, $R_L = 10 k\Omega$

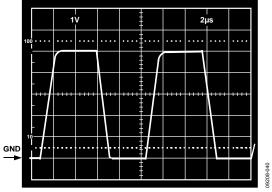


Figure 39. $V_5 = 5 V$, 0 V; Gain-of-2 Inverter Response to 2.5 V Step, Centered -1.25 V Below Ground, $R_L = 10 k\Omega$

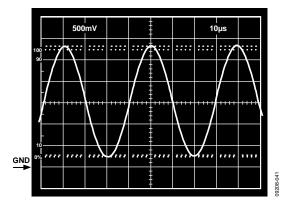
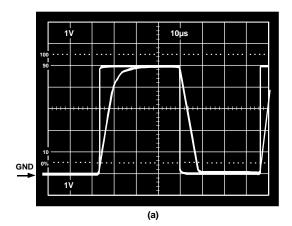
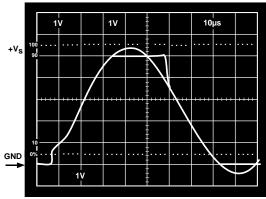
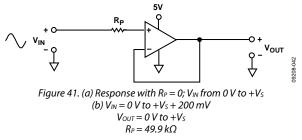


Figure 40. Vs = 3 V, 0 V; Gain-of-2 Inverter, V_{IN} = 1.25 V, 25 kHz, Sine Wave Centered at -0.75 V, R_L = 600 Ω

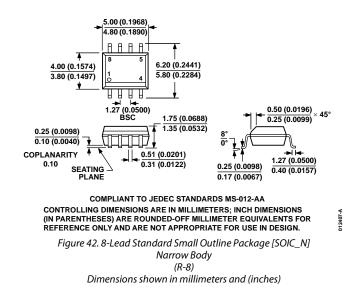








OUTLINE DIMENSIONS



ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Package Option
AD822TRZ-EP	–55°C to +125°C	8-Lead SOIC_N	R-8
AD822TRZ-EP-R7	–55°C to +125°C	8-Lead SOIC_N	R-8

 1 Z = RoHS Compliant Part.

SPICE model is available at www.analog.com.

NOTES

NOTES

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